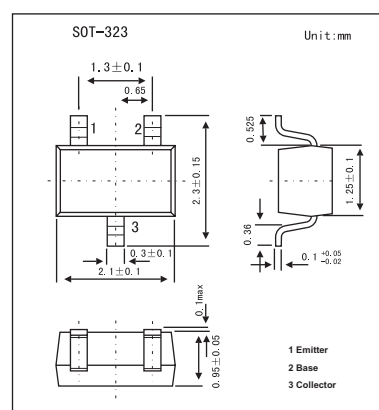


PNP silicon Transistor

2SA1576

■ Features

- Low noise: NF=0.5dB(TYP.)
- Epitaxial planar type.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_c	-100	A
Collector power dissipation	P_c	200	W
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_c = -50\mu\text{A}$	-50			V
Collector-emitter breakdown voltage	BV_{CEO}	$I_c = -1\text{mA}$	-40			V
Emitter-base breakdown voltage	BV_{EBO}	$I_E = -50\mu\text{A}$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -30\text{V}$			-0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\text{V}$			-0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c/I_B = -50\text{mA}/-5\text{mA}$			-0.5	V
DC current transfer ratio	h_{FE}	$V_{CE} = -6\text{V}, I_c = -1\text{mA}$	120		560	
Transition frequency	f_T	$V_{CE} = -12\text{V}, I_E = 2\text{mA}$		140		MHz
Output capacitance	C_{ob}	$V_{CB} = -12\text{V}, I_E = 0\text{A}, f = 1\text{MHz}$		3.5		pF

■ h_{FE} Classification

Marking	Q	R	S
h_{FE}	120~270	180~390	270~560